

Description

This 45A,30V N-Channel MOSFET in a PDFN5\*6 Plastic Package.

Applications

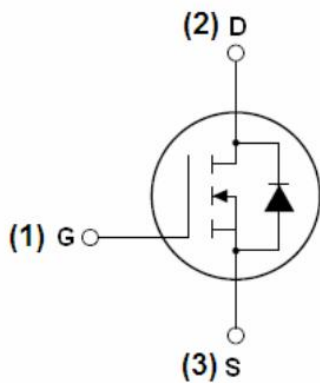
Battery Management

Features

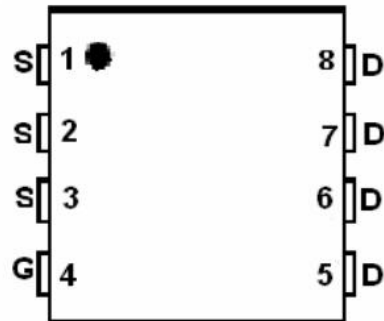
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- Halogen-free Product

$V_{DSS}$	$R_{DS(on)}$ Typ	$I_D$
30V	4.5mΩ	45A

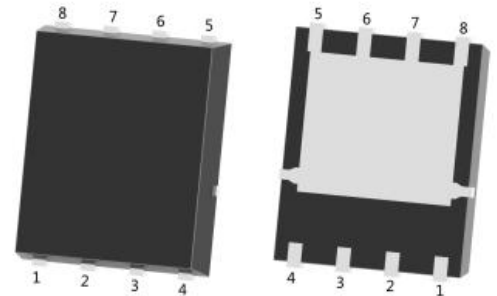
Equivalent Circuit & Pinning



Schematic diagram



Pin assignment



PDFN5X6-8L

**Absolute Maximum Ratings(Ta=25°C)**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Drain Current - Continuous	I <sub>D</sub>	45	A
Drain Current – Pulsed	I <sub>DM</sub>	135	A
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Power Dissipation	P <sub>D</sub> (T <sub>c</sub> =25°C)	28	W
Single Pulse Avalanche Energy(L=0.5mH)	E <sub>AS</sub>	211	mJ
Avalanche Current(L=0.5mH)	I <sub>AS</sub>	23	A
Junction and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	°C
Thermal resistance, junction - ambient	t ≤ 10s	R <sub>θJA</sub>	°C/W
	Steady-State		
Thermal resistance, junction - case	Steady-State	R <sub>θJC</sub>	4.5

**Electrical Characteristics(Ta=25°C)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250uA, V <sub>GS</sub> =0V	30	33		V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1.0	uA
Gate-Body leakage current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V			±10 0	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	1.7	2.5	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A		4.5	6	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A		7	9	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V V <sub>GS</sub> =0V f=1.0MHz		2090		pF
Output Capacitance	C <sub>oss</sub>			790		
Reverse Transfer Capacitance	C <sub>rss</sub>			634		
Gate resistance	R <sub>g</sub>	V <sub>GS</sub> =0V V <sub>DS</sub> =0V f=1MHz		1.9		Ω
Total Gate Charge	Q <sub>g</sub> (10V)	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V I <sub>D</sub> =20A		37		nC
Total Gate Charge	Q <sub>g</sub> (4.5V)			18		
Gate Source Charge	Q <sub>gs</sub>			4.8		
Gate Drain Charge	Q <sub>gd</sub>			11		

**Electrical Characteristics(Ta=25°C)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V,$ $R_L=0.75\Omega, R_{GEN}=3\Omega$		8.1		ns
Turn-On Rise Time	$t_r$			8.6		
Turn-Off Delay Time	$t_{D(off)}$			29		
Turn-Off Fall Time	$t_f$			8		

Electrical Characteristic Curve

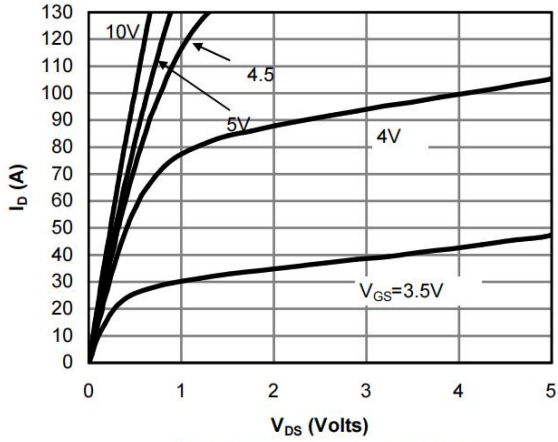


Fig 1: On-Region Characteristics

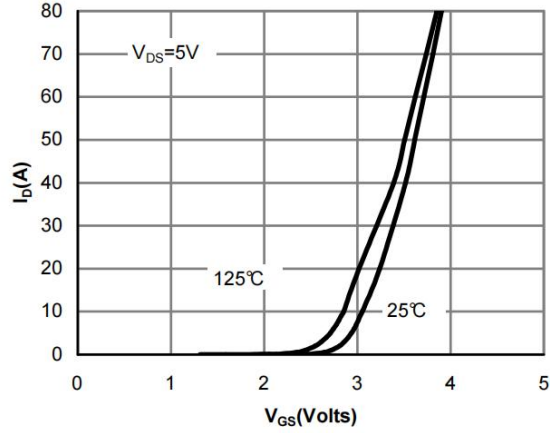


Figure 2: Transfer Characteristics

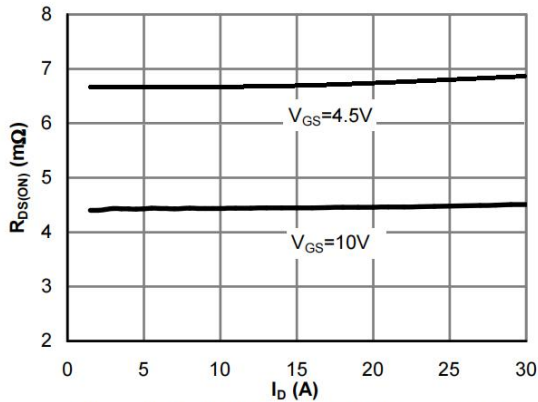


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

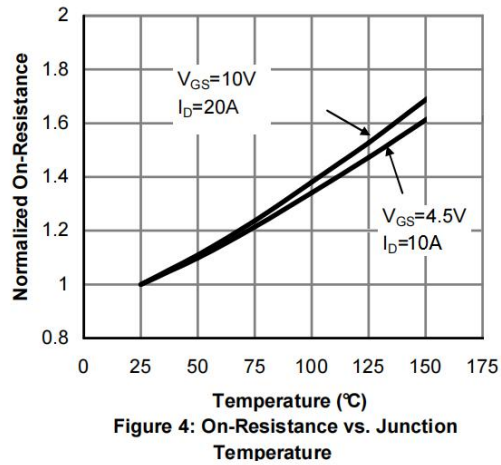


Figure 4: On-Resistance vs. Junction Temperature

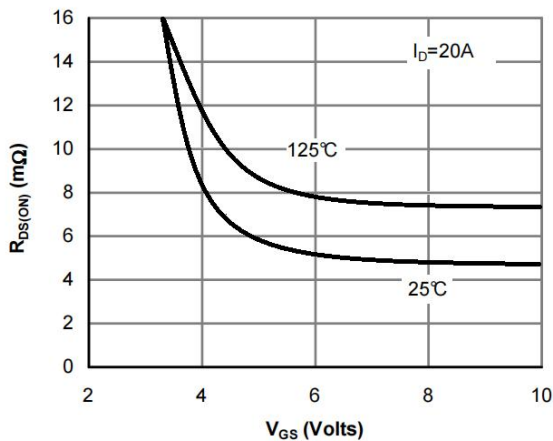


Figure 5: On-Resistance vs. Gate-Source Voltage

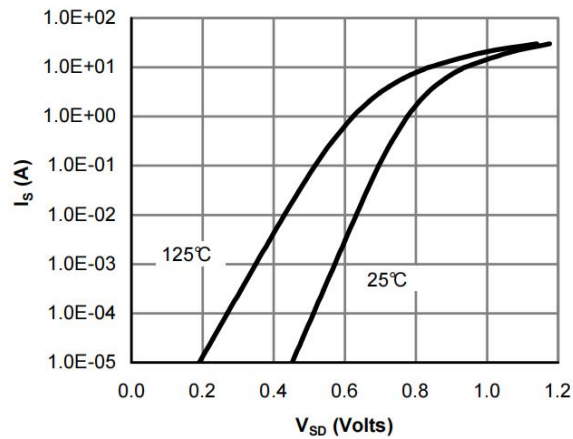


Figure 6: Body-Diode Characteristics

Electrical Characteristic Curve

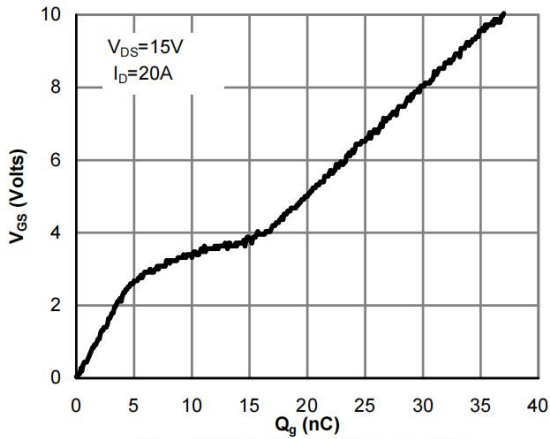


Figure 7: Gate-Charge Characteristics

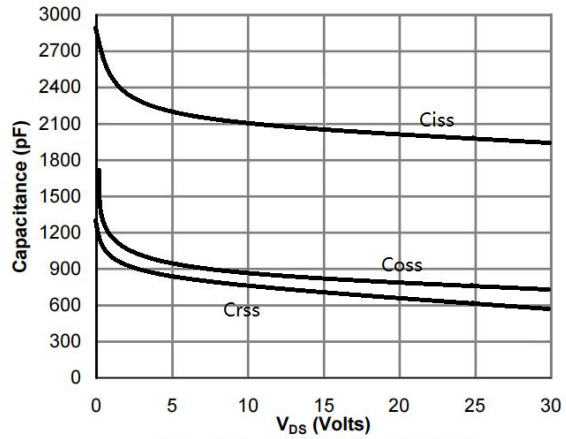


Figure 8: Capacitance Characteristics

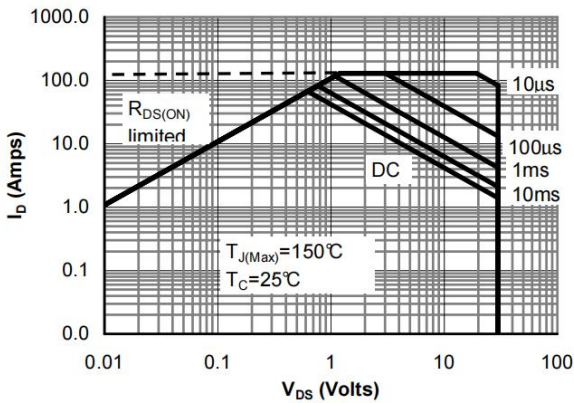


Figure 9: Maximum Forward Biased Safe Operating Area

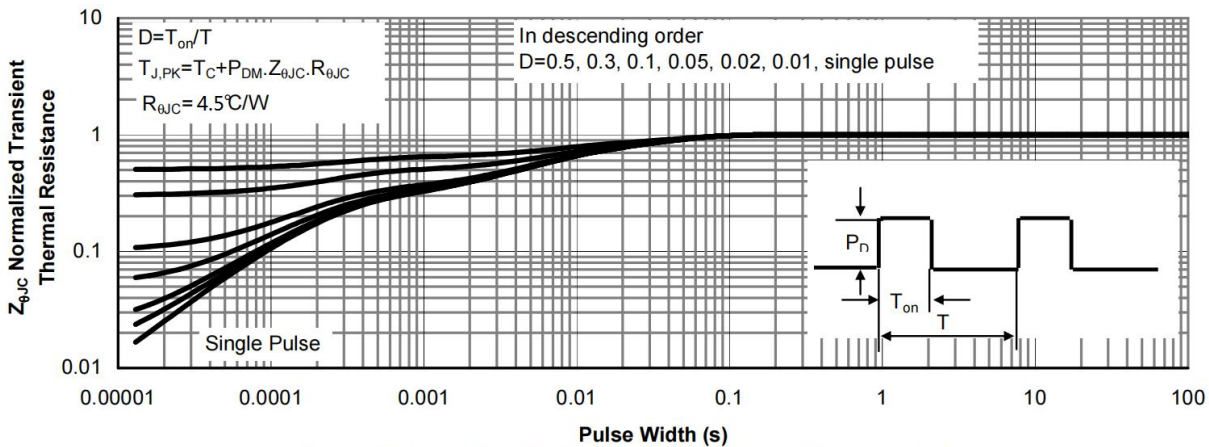
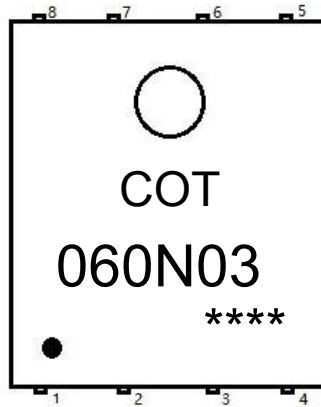


Figure 10: Normalized Maximum Transient Thermal Impedance (Note F)

Marking Instructions



Note:

COT: Company Logo

060N03: Product Type.

\*\*\*\*: Lot No. Code, code change with Lot No.

Packaging SPEC.

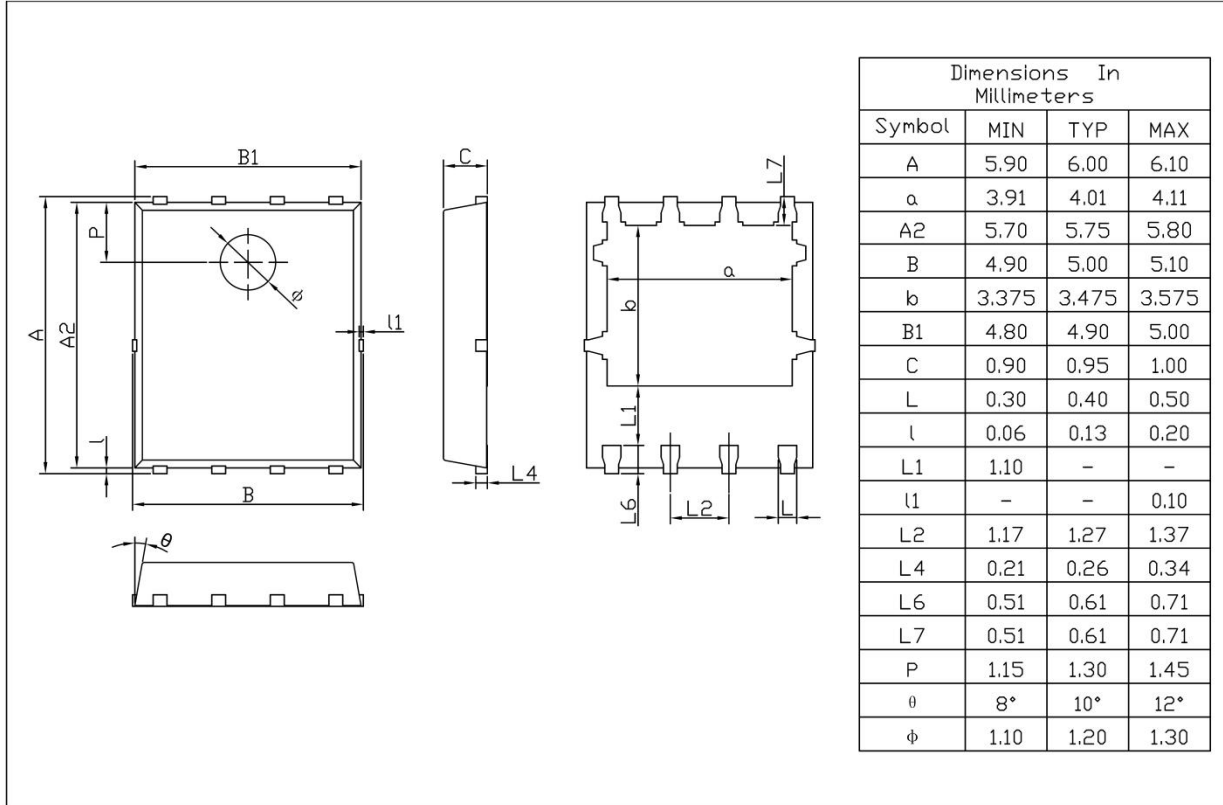
REEL INFORMATION

Package Type	Units					Dimension (unit: mm <sup>3</sup> )		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
PDFN5*6	5000	2	10000	6	60000	13" × 12	360 × 360 × 50	380 × 335 × 366

Package Outline Dimensions

PDFN5 X6

Unit:mm



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